

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	4mΩ @ V _{GS} = 10V	19A
	7.25mΩ @ V _{GS} = 4.5V	14A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- General-purpose interfacing switches
- Power-management functions

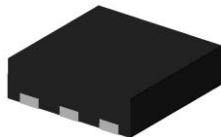
Features

- Low Gate Threshold Voltage
- Low On-Resistance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

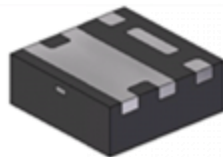
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.0065 grams (Approximate)

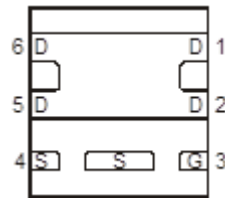
U-DFN2020-6 (Type E)



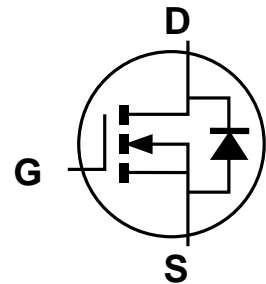
Top View



Bottom View



Pin Out
Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMT34M8LFDE-7	U-DFN2020-6 (Type E)	3,000	Tape & Reel
DMT34M8LFDE-13	U-DFN2020-6 (Type E)	10,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



T3 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 3 = 2023)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	1	2	3	4	5	6	7	8	9	0	1	2

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	Steady State	T _A = +25°C	19
		T _A = +70°C	15
Maximum Body Diode Forward Current	I _S	3.1	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	88	A
Pulsed Drain Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)	I _{SM}	88	A
Avalanche Current (L = 0.1mH) (Note 6)	I _{AS}	25	A
Avalanche Energy (L = 0.1mH) (Note 6)	E _{AS}	31	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P _D	1.1	W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	110	°C/W
Total Power Dissipation (Note 5)	Steady State	P _D	2.2
		R _{θJA}	55
Thermal Resistance, Junction to Case (Note 8)	R _{θJC}	6.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.5	4	mΩ	V _{GS} = 10V, I _D = 10A
			6	7.25		V _{GS} = 4.5V, I _D = 10A
Diode Forward Voltage	V _{SD}	—	0.7	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1024	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	876	—		
Reverse Transfer Capacitance	C _{rss}	—	50	—		
Gate Resistance	R _g	—	1.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	7.3	—	nC	V _{DD} = 15V, I _D = 9A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	15.4	—		
Gate-Source Charge	Q _{gs}	—	2.9	—		
Gate-Drain Charge	Q _{gd}	—	2.0	—		
Turn-On Delay Time	t _{D(ON)}	—	3.1	—	ns	V _{DD} = 15V, V _{GS} = 10V R _g = 3Ω, I _D = 9A
Turn-On Rise Time	t _r	—	3.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	16.6	—		
Turn-Off Fall Time	t _f	—	5.3	—		
Reverse Recovery Time	t _{RR}	—	29.4	—	ns	I _F = 1.5A, dI/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	19.2	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

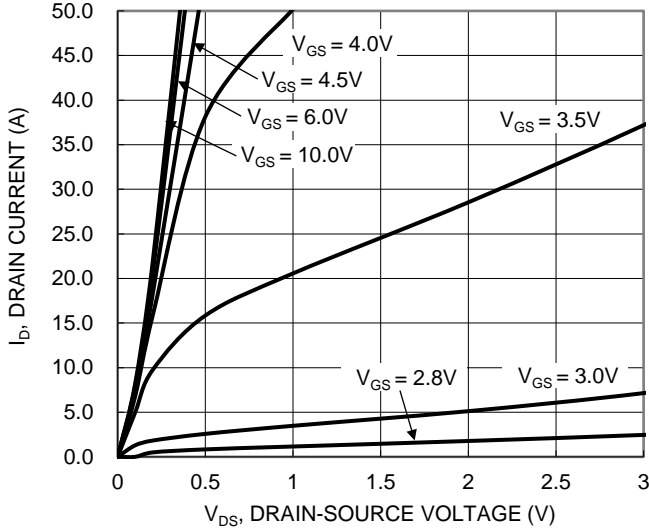


Figure 1. Typical Output Characteristic

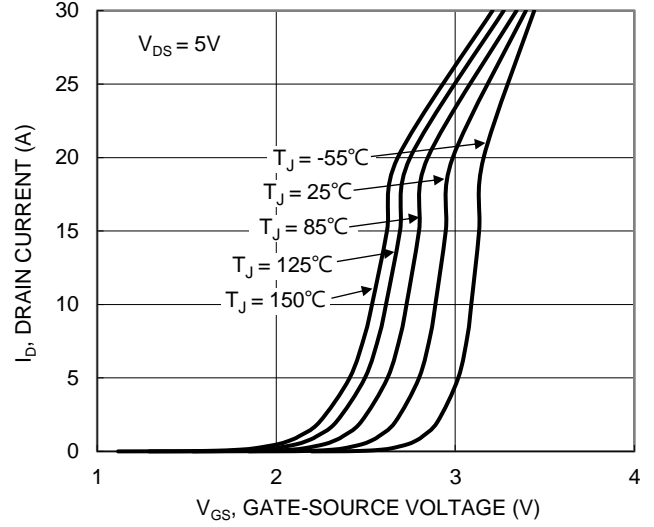


Figure 2. Typical Transfer Characteristic

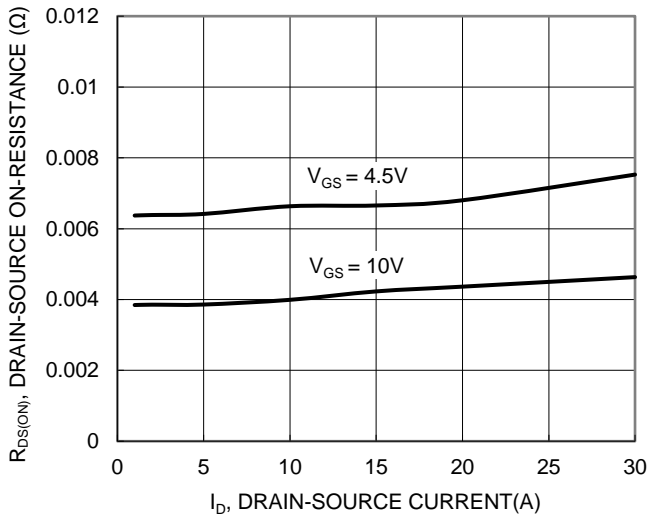


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

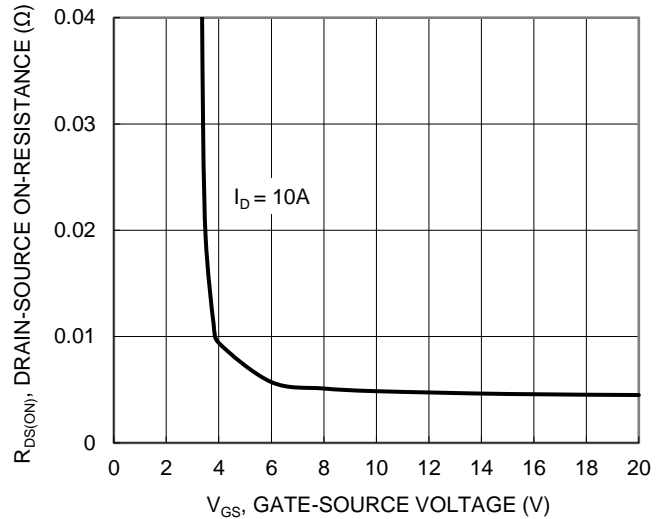


Figure 4. Typical Transfer Characteristic

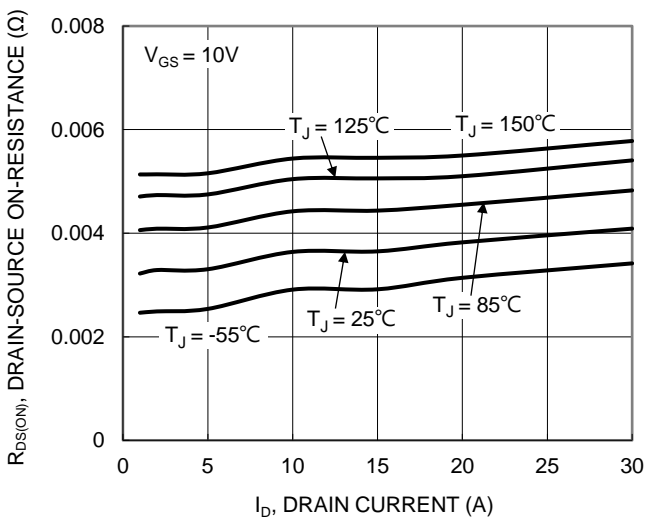


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

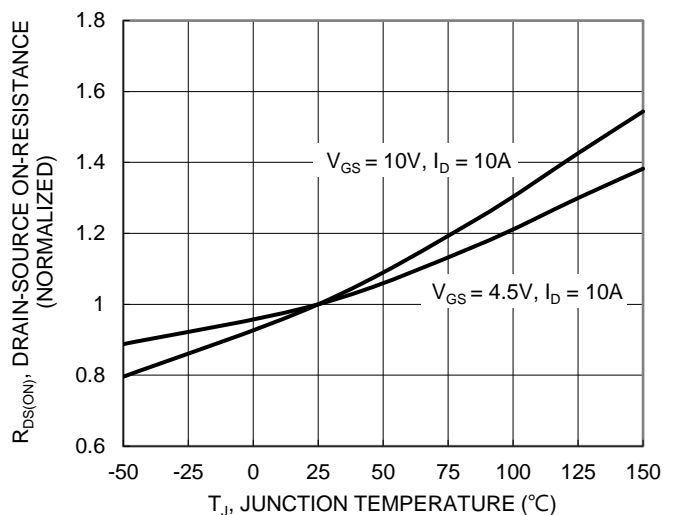


Figure 6. On-Resistance Variation with Junction Temperature

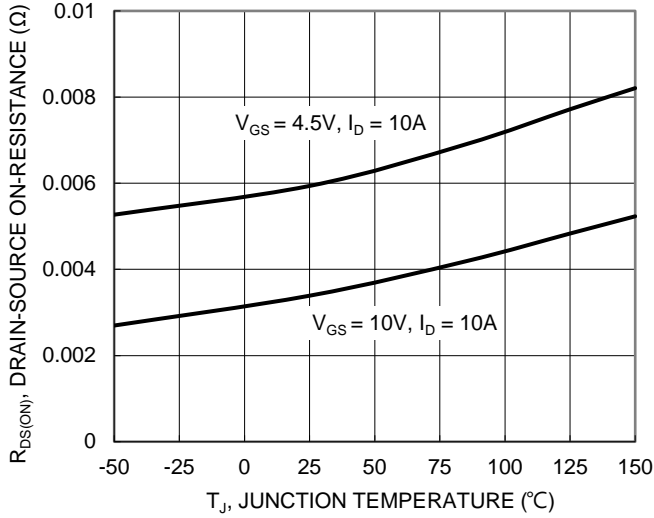


Figure 7. On-Resistance Variation with Junction Temperature

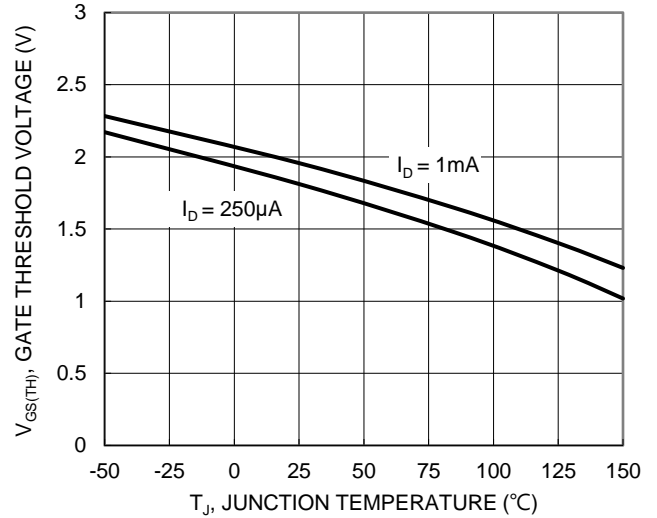


Figure 8. Gate Threshold Variation vs. Junction Temperature

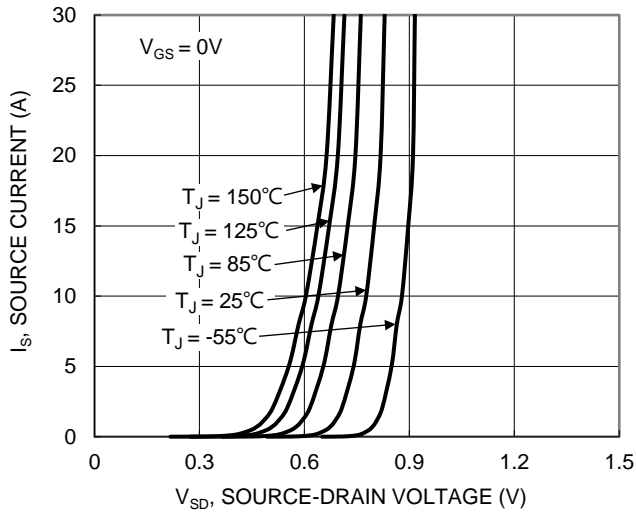


Figure 9. Diode Forward Voltage vs. Current

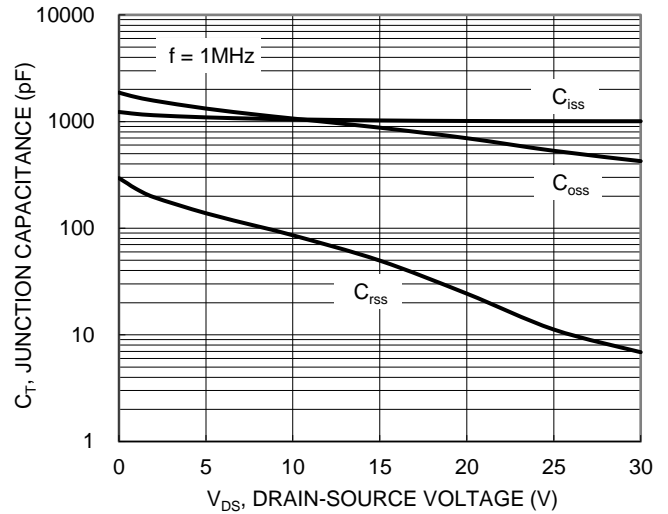


Figure 10. Typical Junction Capacitance

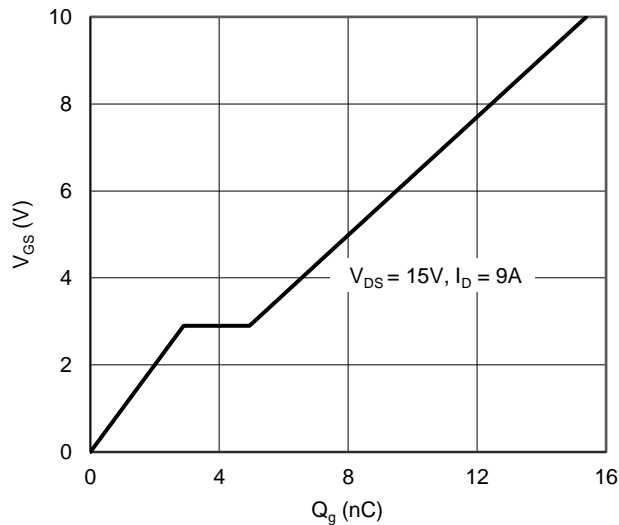


Figure 11. Gate Charge

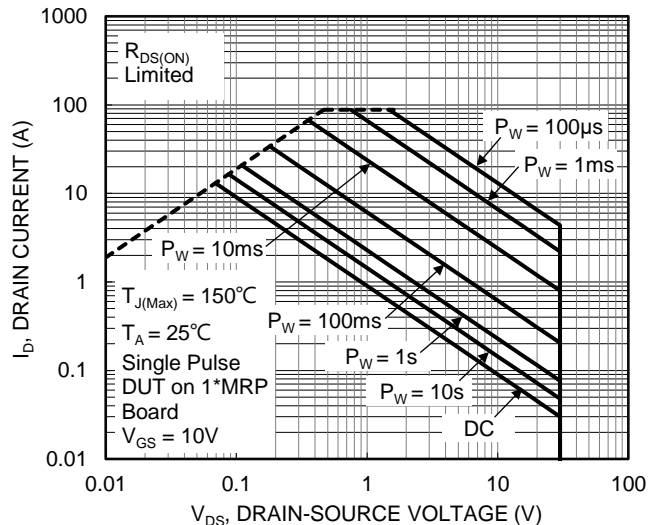


Figure 12. SOA, Safe Operation Area

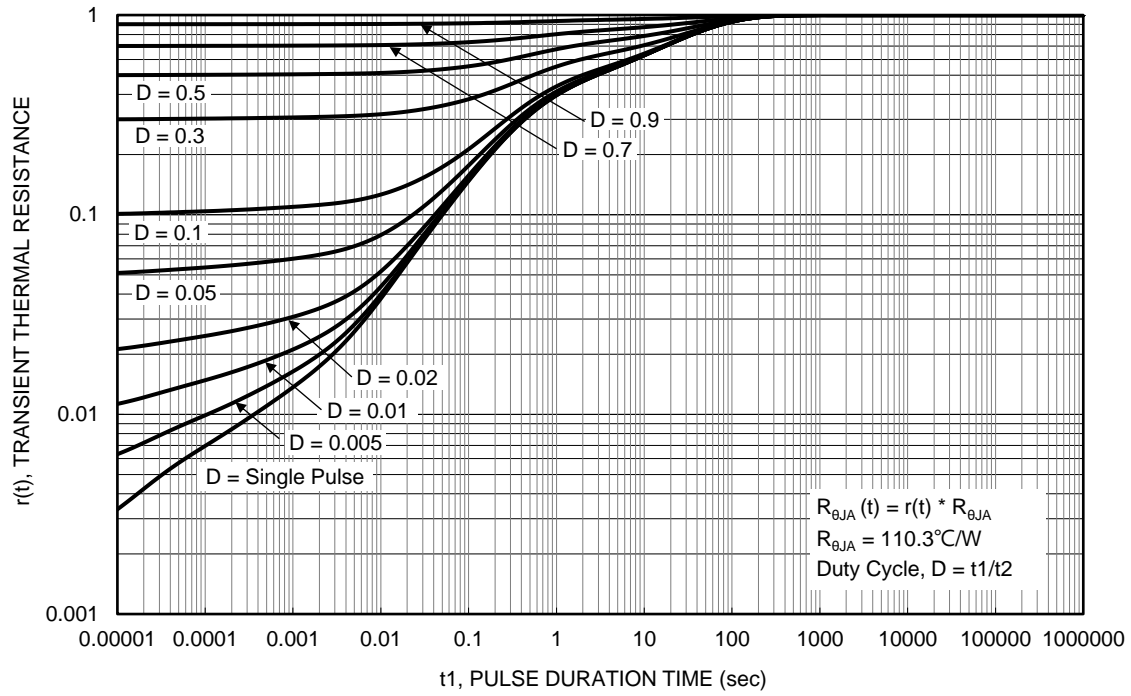
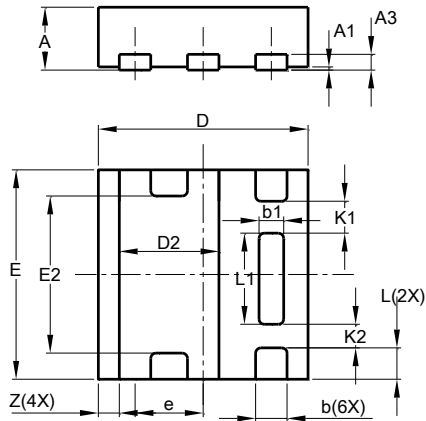


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)

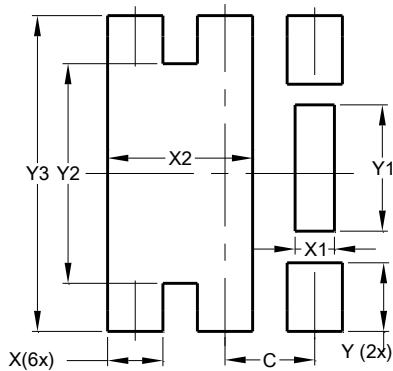


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	–	–	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	–	–	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	–	–	0.305
K2	–	–	0.225
Z	–	–	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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